

2MBI1200U4G-120

IGBT Modules

IGBT MODULE (U series) 1200V / 1200A / 2 in one package

Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



■ Maximum Ratings and Characteristics

■ Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items		Symbols	Conditions		Maximum ratings	Units	
Collector-Emitter voltage		Vces			1200	V	
Gate-Emitter voltage		Vges			±20	V	
Collector current		Ic	Continuous	Tc=25°C	1600		
			Continuous	Tc=80°C	1200		
		Ic pulse	1ms	Tc=25°C	3200	^	
				Tc=80°C	2400	Α	
		-lc					
		-lc pulse	1ms		2400		
Collector power dissipation		Pc	1 device	1 device		W	
Junction temperature		Tj			150	°C	
Storage temperature		Tstg			-40 ~ +125	l C	
Isolation voltage Between termina	ation voltage Between terminal and copper base (*1)		AC : 1min.		4000	VAC	
Mounting (*2)	··· · · · · · · · · · · · · · · · · ·	M6			5.75		
Screw torque	Terminals (*3)	M8			10	N m	
ierminais (*3)		M4			2.5		

Note *1: All terminals should be connected together when isolation test will be done.

Note *2: Recommendable Value: Mounting 4.25~5.75 Nm (M6)

Note *3: Recommendable Value: Main Terminals 8~10 Nm (M8)

Sense Terminals 1.7~2.5 Nm (M4)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

Itama	Cumbala	Symbols Conditions		Characteristics			Units	
Items	Symbols			min.	typ.	max.	Units	
Zero gate voltage collector current	Ices	V _{GE} = 0V, V _{CE} = 1200V		-	-	1.0	mA	
Gate-Emitter leakage current	Iges	$V_{CE} = 0V$, $V_{GE} = \pm 20V$		-	-	1600	nA	
Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _C = 1200mA		5.5	6.5	7.5	V	
	V _{CE} (sat)		Tj=25°C	-	2.22	2.41	V	
Callactar Emitter activation valtage	(main terminal)	V _{GE} = 15V	Tj=125°C	-	2.42	-		
Collector-Emitter saturation voltage	V _{CE} (sat)	Ic = 1200A	Tj=25°C	-	1.90	2.05		
	(chip)		Tj=125°C	-	2.10	-		
Input capacitance	Cies	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz		-	135	-	nF	
T	ton	$V_{cc} = 600V$ R _{gon} = 3.3 Ω		-	1.35	-		
Turn-on	tr	$I_{c} = 1200A$ $R_{soff} = 0.82\Omega$		-	0.65	-	1	
T eff	toff	V _{GE} = ±15V		-	0.80	-	μs	
Turn-off	tf	Tj = 125°C		-	0.20	-		
	V _F		Tj=25°C	-	1.97	2.16	V	
Famusard on voltage	(main terminal)	V _{GE} = 0V I _F = 1200A	Tj=125°C	-	2.07	-		
Forward on voltage	V _F		Tj=25°C	-	1.65	1.80		
	(chip)		Tj=125°C	-	1.75	-		
Reverse recovery	trr	I _F = 1200A	* -	-	0.45	-	μs	
Lead resistance, terminal-chip	R lead			-	0.27	3450	mΩ	

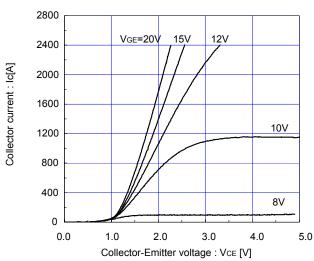
Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
items		Conditions	min.	typ.	max.	Ullits
Thermal registeres (1device)	Dth/i o)	IGBT	-	-	0.020	°C/W
Thermal resistance (1device)	Rth(j-c)	FWD	-	-	0.033	
Contact thermal resistance (1device)	Rth(c-f)	with Thermal Compound (*4)	-	0.006	-	

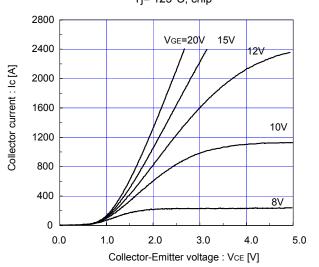
Note *4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

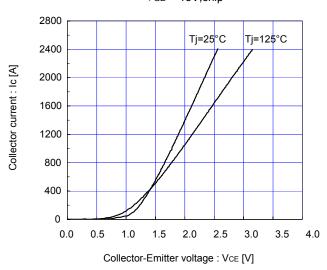
Collector current vs. Collector-Emitter voltage (typ.) Tj=25°C,chip



Collector current vs. Collector-Emitter voltage (typ.) Tj= 125°C, chip

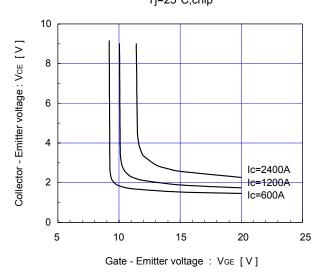


Collector-Emitter voltage vs. Gate-Emitter voltage (typ.) V_{GE}=+15V,chip

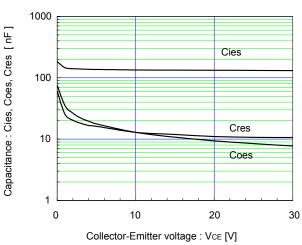


Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)

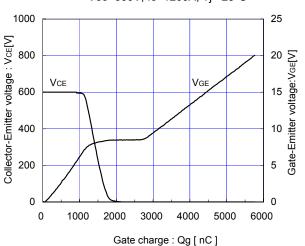
Tj=25°C,chip



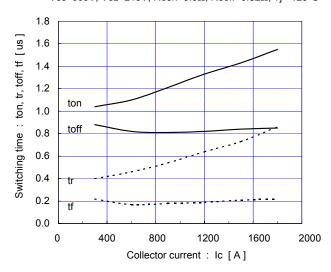
Capacitance vs. Collector-Emitter voltage (typ.) VGE=0V, f= 1MHz, Tj= 25°C



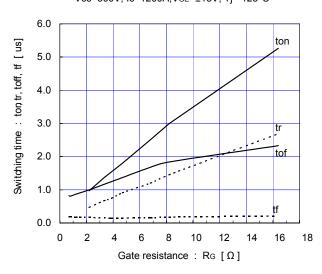
Dynamic Gate charge (typ.) Vcc=600V, lc=1200A, Tj= 25°C



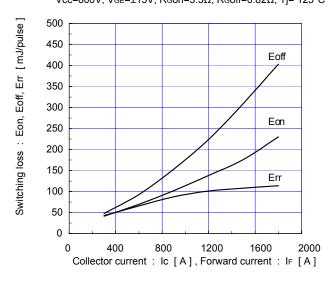
Switching time vs. Collector current (typ.) Vcc=600V, VeE= \pm 15V, Reon=3.3 Ω , Reoff=0.82 Ω , Tj= 125°C



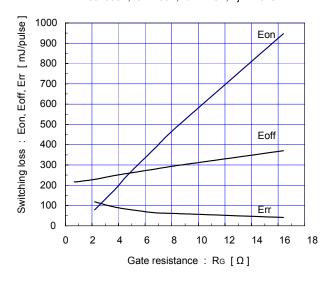
Switching time vs. Gate resistance (typ.) Vcc=600V, Ic=1200A,VcE=±15V, Tj= 125°C



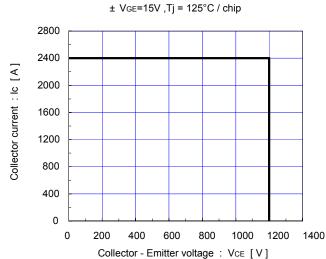
Switching loss vs. Collector current (typ.) Vcc=600V, VgE=±15V, Rgon=3.3Ω, Rgoff=0.82Ω, Tj= 125°C



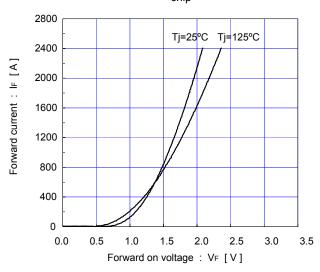
Switching loss vs. Gate resistance (typ.) Vcc=600V, Ic=1200A,VgE=±15V, Tj= 125°C



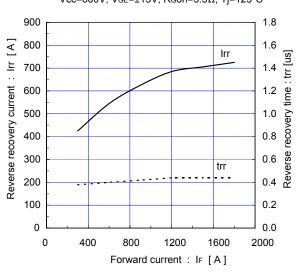
Reverse bias safe operating area (max.)



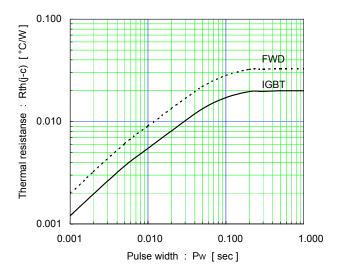
Forward current vs. Forward on voltage (typ.)



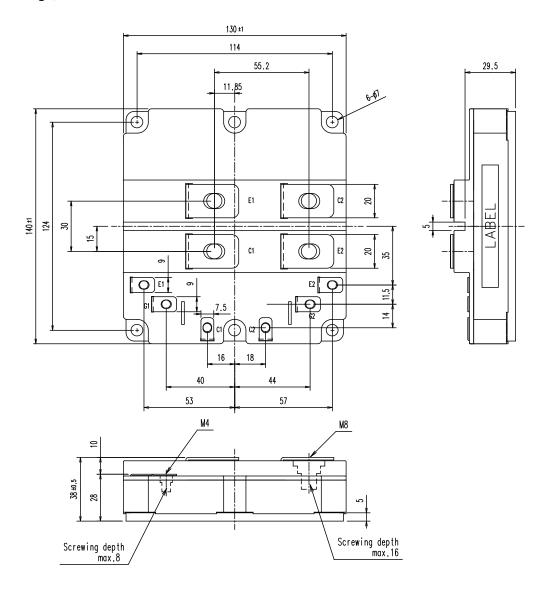
Reverse recovery characteristics (typ.) Vcc=600V, VgE= \pm 15V, Rgon= 3.3Ω , Tj= 125° C



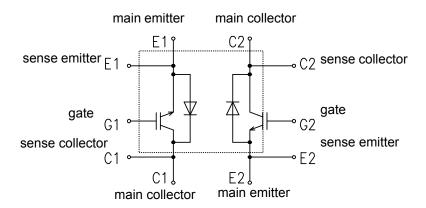
Transient thermal resistance (max.)



■ Outline Drawings, mm



■ Equivalent Circuit Schematic



http://www.fujielectric.com/products/semiconductor/

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